

Feedback for EEE6215 Session: 2015-2016

Feedback: Please write simple statements about how well students addressed the exam paper in general and each individual question in particular including common problems/mistakes and areas of concern in the boxes provided below. Increase row height if necessary.

General Comments:

Marks somewhat lower than expectations and will be subject to a small pedestal. Average lowest in 3 years. Some evidence of too much exam content, leading to poor or incomplete final questions. Some evidence of a slight disconnect between the lecture content and the examination. Coursework marks v. good.

Question 1:

A suggestion that the pre-amble to the question has put a few students off (it should have not done, it's quite easy). Reasonable scores, but some students clearly don't know all the scaling rules and there are some odd and rather random responses. Good descriptions of technology directions

Question 2:

Good scores for a) and sb). Some students confused the HFET with the HBT or gave some very odd descriptions. Not many understood the different types of HFET

Question 3:

Good diagrams in a) and b). Many gave a good general description of the DRAM, but could not explain its function in a circuit and could not make calculations based on this

Question 4:

A decent set of answers for a), but part b) was a real struggle and was marked very generously. Probably too much of an intricate calculation for an exam. Surprising that so many students could not describe an Impatt diode or make what are very basic calculations on it.

Question 5:

A good set of marks, but with a few errors, which often then get compounded. Not much knowledge of practical materials combinations.

Question 6:

A mixed set of results- good for some, but poor for others. This should be pretty straightforward calculations, based on extensive coverage in the lectures. Also this question is pretty common across many past exams. Students may have been under time pressures.

Question 7:

Question 8: